

Product Overview

NGTB40N120FL2: IGBT, 1200V 40A FS2 Solar/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 10 μs Short Circuit Capability

Applications

- Solar Inverter
- Uninterruptible Power Inverter Supplies (UPS)
- Welding

End Products

- Welders
- UPS Systems
- PV Inverters

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	$V_{CES}^{(BR)}$ Typ (V)	I_C Max (A)	$V_{CE(s)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
NGTB40N120FL2WG	2.5333	Pb-free Halide free	Active	1200	40	2	2	1.1	3.4	240	18	313	10	-	535	Yes	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 4/4/2020